

SENSING PROPERTIES AND CATALYTIC DECOMPOSITION TO CHLORINATED HYDROCARBONS OF INDIUM OXIDE BASED GAS SENSORS

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Chlorinated hydrocarbons are typical air pollutants having long-term toxicity. Recently, there are increasing demands for environmental monitoring of chlorinated hydrocarbons in Japan. Thus, the compact gas sensors are needed for this purpose. In this study, the semiconductor gas sensors using In₂O₃-based thin films have been investigated for the detection of 8 kinds of chlorinated hydrocarbons (CCl₄, CHCl₃, CH₂Cl₂, C₂Cl₄, C₂HCl₃, 1,1-C₂H₂Cl₂, C₂H₃Cl, 1,2-C₂H₄Cl₂). As a result, CuO-In₂O₃ sensor could detect CCl₄ with high sensitivity as well as high selectivity. Further, the sensing mechanism to CCl₄ of CuO-In₂O₃ sensor was elucidated by the study on decomposition of CCl₄.

In₂O₃ was prepared from InCl₃ · 4H₂O by wet process. In order to modify with 13 kinds of foreign oxides, In₂O₃ were impregnated with mainly metal acetates. The compact sensor chips equipped with heater were fabricated by using In₂O₃-based powders and subjected to the measurement of sensing properties to 8 kinds of chlorinated hydrocarbons (30 ppm) at 200-400 °C.

Figure 1 shows the sensitivities (Ra/Rg) of In₂O₃-based sensors to 30 ppm CCl₄. Most of In₂O₃ based sensors showed the sensitivity higher than unity, suggesting the response with resistance decrease. Among these, La₂O₃-, Nd₂O₃-, and NiO-In₂O₃ sensors exhibited high sensitivity to CCl₄. On the other hand, only CuO-In₂O₃ sensor showed the large response with resistance increase (Ra/Rg < 1). Further, the CuO-In₂O₃ sensor did not respond to other 7 chlorinated hydrocarbons expect for CCl₄, as shown in Fig. 2, suggesting high selectivity to CCl₄ of CuO-In₂O₃ sensor. When the loading of CuO was changed, the optimal loading was found to be 0.1 wt% and the highest sensitivity of 0.03 (=Ra/Rg) was obtained to 30 ppm CCl₄ at 200 °C.

In order to elucidate the sensing mechanism of CuO-In₂O₃, CCl₄ decomposition was carried out on In₂O₃ and CuO-In₂O₃. Figure 3 shows the conversion in CCl₄ decomposition on In₂O₃ based catalysts as a function of temperature. The catalytic activity was the lowest for pure In₂O₃ catalyst. The activity slightly increased when 0.01 wt% CuO was added to In₂O₃, and 0.1 and 5 wt% CuO-In₂O₃ showed the highest activity, suggesting that the modification with CuO enhanced the catalytic activity of In₂O₃ in CCl₄ decomposition. The amounts of CO₂ produced in CCl₄ decomposition are shown in Fig. 4. CO₂ was produced even in low conversion range on In₂O₃ and 0.01 wt% CuO-In₂O₃, while any CO₂ was not produced on 0.1 wt% CuO-In₂O₃ until the conversion reached 60% and kept in low level until 95% conversion. CO₂ was moderately observed on 5 wt% CuO-In₂O₃. CCl₄ is decomposed on sensor surface into C and Cl fragments. The C fragment reacts with adsorbed oxygen to form CO₂, inducing the resistance decrease. On the other hand, the Cl fragment is negatively adsorbed on the surface to increase the sensor resistance. On 0.1 wt% CuO-In₂O₃ sensor, CCl₄ is well decomposed into C and Cl fragments. The Cl fragments produce Cl adsorbates but the C fragments are not oxidized. The formation of Cl adsorbates effectively contribute to the large resistance increase of 0.1 wt% CuO-In₂O₃.

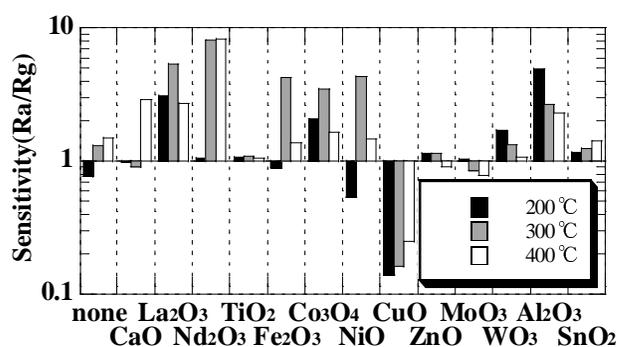


Fig. 1 Sensitivities of In₂O₃ based thin film sensors doped with various metal oxides to 30 ppm CCl₄ at 200-400 °C.

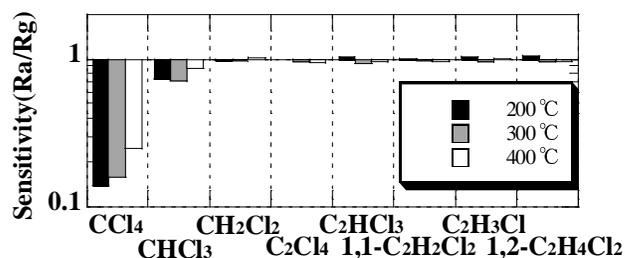


Fig. 2 Sensitivities to 30 ppm various chlorinated hydrocarbons of 5 wt% CuO-In₂O₃ sensor at 200-400 °C.

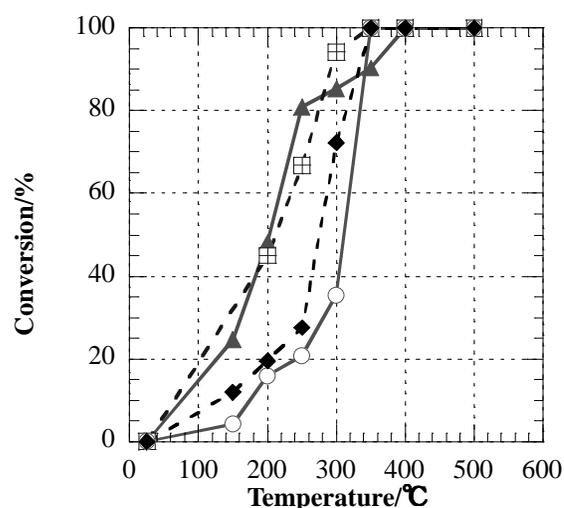


Fig. 3 Conversion in CCl₄ decomposition on In₂O₃ based catalysts as a function of temperature

—○— : In₂O₃, —◆— : 0.01 wt% CuO-In₂O₃,
 - -□ - - : 0.1 wt% CuO-In₂O₃,
 —▲— : 5 wt% CuO-In₂O₃.

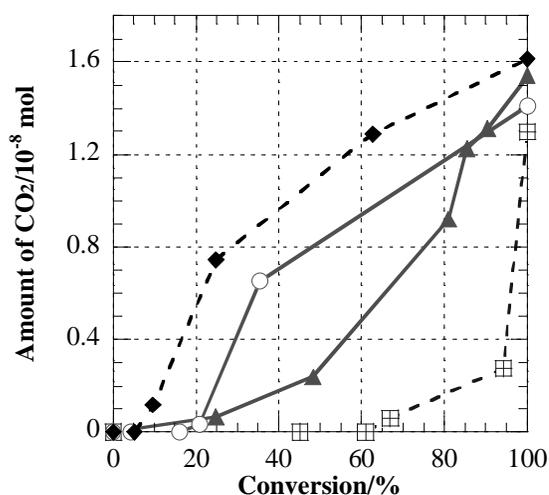


Fig. 4 Amount of CO₂ produced in CCl₄ decomposition on In₂O₃ based catalysts as a function of conversion.

—○— : In₂O₃, —◆— : 0.01 wt% CuO-In₂O₃,
 - -□ - - : 0.1 wt% CuO-In₂O₃,
 —▲— : 5 wt% CuO-In₂O₃.